

REMARKS

Claims 1-25 are pending in this application. Claims 7, 11 and 17 were previously withdrawn from consideration. By this Amendment, claims 1-4, 8-10, 12-14, 18-20 and 22 are amended.

I. Formal Drawings

The Office Action approves the proposed drawing correction filed on December 19, 2002, but fails to acknowledge the Letter to the Official Draftsperson filed May 29, 2003. Accordingly, formal drawings 24-26C are resubmitted herewith to obviate the requirement for corrected drawings. Applicants respectfully request acceptance of the drawings filed herewith.

II. The Claims Define Patentable Subject Matter

The Office Action rejects claims 1-6, 8-10, 12-16 and 18-25 under 35 U.S.C. §103(a) over U.S. Patent No. 5,824,186 to Smith et al. in view of the specification disclosure at paragraphs 3-11; and claims 1-6, 8-10, 12-16 and 18-25 under 35 U.S.C. §103(a) over Smith et al., the specification disclosure at paragraphs 9-11, and WO 99/12170. These rejections are respectfully traversed.

Smith et al. does not teach, disclose or suggest "a passive matrix array that includes "memory cells formed of ferroelectric capacitors, a ferroelectric capacitor being defined by an intersection of row and column electrodes sandwiching a ferroelectric film common to the passive matrix array, the passive matrix array being formed on the microstructure; a substrate, the microstructure being centrally positioned without the aid of a transport fluid and integrated on the substrate," as recited in claim 1, and as similarly recited in claims 2, 3, 8-10, 12-14, 18 and 19.

Furthermore, Smith et al. does not disclose a passive matrix array and a peripheral circuit including at least a word line driver circuit and a bit line driver circuit for driving the passive matrix array.

According to the claimed invention, a passive matrix array and a peripheral circuit including a word line driver circuit and a bit line driver circuit may be fabricated separately. Therefore, the peripheral circuit of the claimed invention would not be adversely affected by the fabrication of the passive matrix array, thereby decreasing the limitation and improving the fabricating process. Smith et al. does not disclose these features and advantages of the features.

The specification disclosure at paragraphs 3-11 does not make up for the deficiencies of Smith et al. Instead, the specification disclosure at paragraph 5 discloses the limitation of a conventional ferroelectric memory being fabricated by integrating the passive matrix array and the peripheral circuits on a single substrate in one plane. The specification disclosure at paragraphs 9-11 describe the problems with such conventional ferroelectric memory, the conventional fabrication process being limited to a large extent as disclosed.

WO 99/12170 does not make up for the deficiencies of Smith et al. Instead, WO 99/12170 merely describes a conventional ferroelectric data processing device with a ferroelectric thin film provided between a first and a second electrode structure.

Even if combined, Smith et al., the specification disclosure at paragraphs 3-11, and WO 99/12170 do not combine to result in the claimed features as recited above.

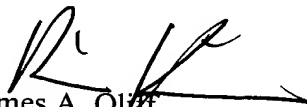
For at least these reasons, it is respectfully submitted that claims 1-3, 8-10, 12-14, 18 and 19 are patentable over the applied references. The dependent claims are likewise patentable over the applied references for at least the reasons discussed, as well as for the additional features they recite. Applicants respectfully request that the rejections under 35 U.S.C. §103(a) be withdrawn.

III. Conclusion

In view of the foregoing, it is respectfully submitted that this application is in condition for allowance. Favorable reconsideration and prompt allowance of claims 1-25 are earnestly solicited.

Should the Examiner believe that anything further would be desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact the undersigned at the telephone number set forth below.

Respectfully submitted,


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Attachment:
Drawings

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